

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1456** is Designed for Television Band III Applications up to 225 MHz.

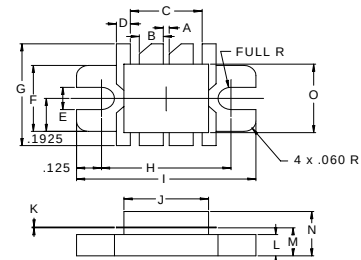
FEATURES:

- Common Emitter
- $P_G = 11$ dB at 100 W/225 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	16 A
V_{CBO}	65 V
V_{CEO}	33 V
V_{EBO}	3.5 V
P_{DISS}	150 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	0.8°C/W

PACKAGE STYLE .400 8L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.030 / 0.76	
B	.115 / 2.92	.125 / 3.18
C	.360 / 9.14	
D	.065 / 1.65	.075 / 1.91
E	.130 / 3.30	
F	.380 / 9.65	.390 / 9.91
G	.735 / 18.67	.765 / 19.43
H	.645 / 16.38	.655 / 16.64
I	.895 / 22.73	.905 / 22.99
J	.420 / 10.67	.430 / 10.92
K	.003 / 0.08	.007 / 0.18
L	.120 / 3.05	.130 / 3.30
M	.159 / 4.04	.175 / 4.45
N		.280 / 7.11
O	.395 / 10.03	.405 / 10.29

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 50$ mA	65			V
BV_{CER}	$I_C = 50$ mA $R_{BE} = 15 \Omega$	60			V
BV_{CEO}	$I_C = 50$ mA	33			V
BV_{EBO}	$I_E = 5.0$ mA	3.5			V
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	20		150	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz	---	60	---	pF
P_G	$V_{CE} = 28$ V $I_C = 2 \times 100$ mA $f = 225$ MHz $P_{OUT} = 100$ W	11			dB